

Giuseppe Greco received the M.Sc. Degrees in Physics from the University of Catania (Italy) in 2009. In 2010 joined CNR-IMM as PhD student and in 2013 received the Ph.D. degree in Nanoscience from the Scuola Superiore of the University of Catania, with a thesis on “AlGaN/GaN heterostructures for enhancement mode transistors”, awarded for the outstanding work carried out during the Ph.D. From March 2013 to January 2017 he was post-doc fellow at CNR-IMM in Catania, where he holds a Tenure Track Researcher position since February 2017. From December 2018 he is staff Researcher at CNR-IMM.

His research interest is mainly focused on the processing and characterization of semiconductor devices based on Gallium Nitride (GaN) and related wide band gap materials. He is co-author of more than 120 publications on international journals, conference proceedings and review papers with an h-index=30 (source Scopus). He is also co-authors of 4 books chapters and 6 patents and he has given several invited talks and lectures on GaN at international and national conferences. He has been co-chairman of the workshop WOCSDICE 2023 held in in Palermo (Italy), and it is actually Vice-Chairs of the International Conference on Solid State Devices and Materials (SSDM) in the Area 4: Power / High-speed Devices and Material (<https://ssdm.jp/committees.html>)